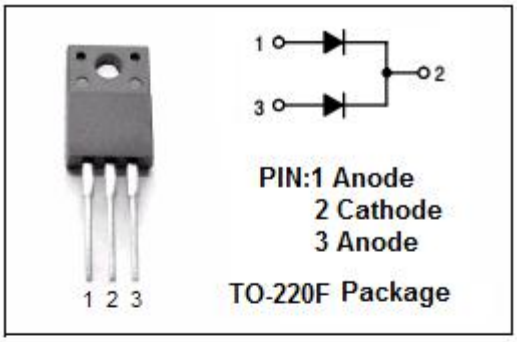
Schottky Barrier Rectifier TSF20U100C

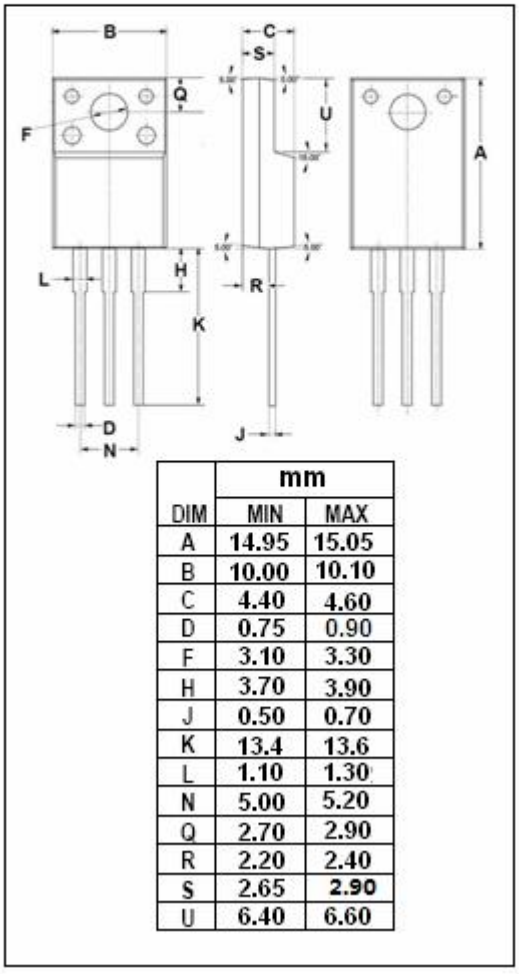
FEATURES

- Plastic material used carriers Underwriter Laboratory
- Metal silicon junction, majority carrier conduction
- Low Power Loss,high Efficiency
- Guard ring for overvoltage protection
- High Surge Capability,High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- For use in low voltage,high frequency inverters,free wheeling and polarity protection applications.



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	100	V
$I_{F(AV)}$	Average Rectified per devics Forward Current per diode	20 10	A
I_{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	150	A
T_J	Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~150	℃
dv/dt	Voltage Rate of Change (Rated V_R)	10000	V/μs

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	4.0	℃/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300μs,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F= 10A ; Tc= 25℃	0.79	V
		I_F= 10A ; Tc= 125℃	0.68	
I_R	Maximum Instantaneous Reverse Current	V_R= $V_{RWM;}$Tc= 25℃	0.5	mA
		V_R= $V_{RWM;}$Tc= 125℃	25	